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- as to the applicant's entitlement to claim the priority of the earlier application (Rule 4.17(iii))

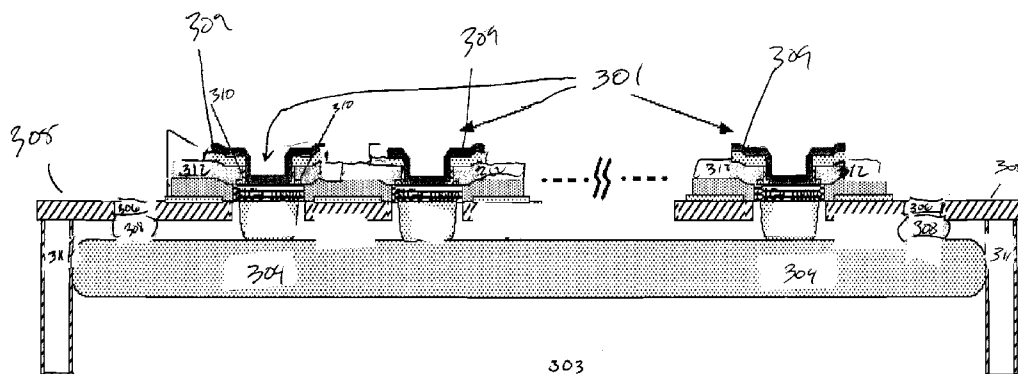
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(54) Title: NPN BIPOLAR TRANSISTOR WITH IMPROVED BASE ACCESS RESISTANCE



(57) Abstract: A configuration composed of multiple short emitters still share common DTI regions and a single big piece of base poly. This allows for base current to flow in 4 directions (e.g., 2 dimensions) as opposed to only two. This significantly reduces the base resistance of the transistor that is crucial for better NPN transistor RF performance and high frequency noise performance.